Ultra-Low Capacitance ESD Protection

Micro-Packaged Diodes for ESD Protection

The ESD7471 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, high breakdown voltage, high linearity, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. It has industry leading capacitance linearity over voltage making it ideal for RF applications. This capacitance linearity combined with the extremely small package and low insertion loss makes this part well suited for use in antenna line applications for wireless handsets and terminals.

Features

• Industry Leading Capacitance Linearity Over Voltage

• Ultra-Low Capacitance: 0.35 pF Max

Stand-off Voltage: 5.3 VLow Leakage: < 1 nA

• Low Dynamic Resistance: $< 1 \Omega$

• IEC61000-4-2 Level 4 ESD Protection

• 1000 ESD IEC61000-4-2 Strikes ±8 kV Contact / Air Discharged

 SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

• RF Signal ESD Protection

• RF Switching, PA, and Antenna ESD Protection

• Near Field Communications

• USB 2.0, USB 3.0

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
IEC 61000-4-2 Contact (ESD) (Note 1) IEC 61000-4-2 Air (ESD) (Note 1)	ESD ESD	±20 ±20	KV kV
IEC 61000-4-5 (ESD) (Note 2)	ESD	2.2	Α
Total Power Dissipation (Note 3) @ T _A = 25°C Thermal Resistance, Junction–to–Ambient	$P_{D} R_{\theta JA}$	300 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. At least 10 discharges at $T_A = 25^{\circ}C$, per IEC61000-4-2 waveform.

2. Non-repetitive current pulse at $T_A = 25^{\circ}C$, per IEC61000-4-5 waveform.

3. Mounted with recommended minimum pad size, DC board FR-4



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MARKING DIAGRAM



XDFN2 CASE 711AM



D = Specific Device Code

M = Date Code

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7471N2T5G	XDFN2 (Pb-Free)	8000 / Tape & Reel
SZESD7471N2T5G	XDFN2 (Pb-Free)	8000 / Tape & Reel

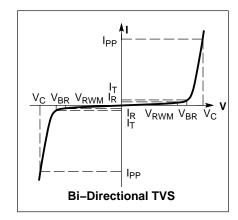
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter	
I _{PP}	Maximum Reverse Peak Pulse Current	
V _C	Clamping Voltage @ IPP	
V_{RWM}	Working Peak Reverse Voltage	
I _R	Maximum Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
I _T	Test Current	

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}				5.3	V
Breakdown Voltage	V_{BR}	I _T = 1 mA (Note 4)	7.0			V
Reverse Leakage Current	I _R	V _{RWM} = 5.3 V		< 1	50	nA
Clamping Voltage	V _C	I _{PP} = 1 A (Note 5)		13	15	V
Junction Capacitance	CJ	$V_R = 0 \text{ V, } f = 1 \text{ MHz}$ $V_R = 0 \text{ V, } f = 1 \text{ GHz}$		0.24 0.24	0.35 0.35	pF
Dynamic Resistance	R _{DYN}	TLP Pulse		0.8		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.
- 5. Non-repetitive current pulse at 25°C, per IEC61000-4-5 waveform.

TYPICAL CHARACTERISTICS

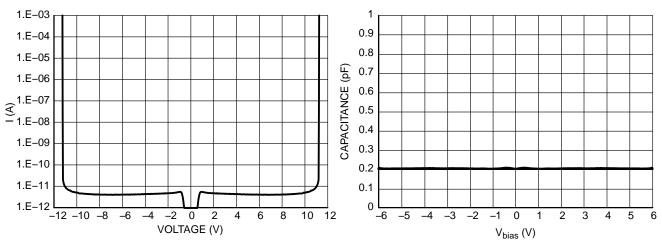


Figure 1. IV Characteristics

Figure 2. CV Characteristics

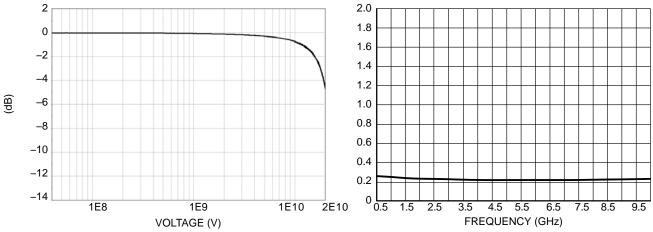


Figure 3. RF Insertion Loss

Figure 4. Capacitance over Frequency

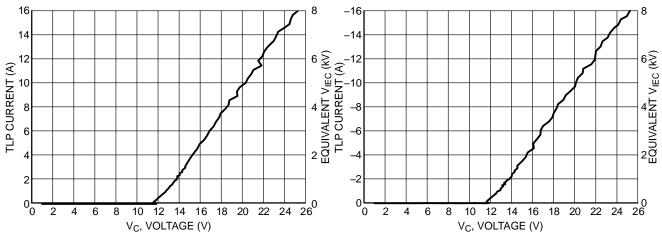
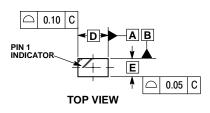


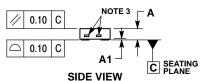
Figure 5. Positive TLP I-V Curve

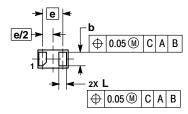
Figure 6. Negative TLP I-V Curve

PACKAGE DIMENSIONS

XDFN2 1.0x0.6, 0.65P (SOD-882)CASE 711AM ISSUE O







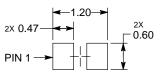
BOTTOM VIEW

NOTES:

- DIMENSIONING AND TOLERANCING PER
 ASME VALUE AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
- EXPOSED COPPER ALLOWED AS SHOWN.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.44	
A1	0.05		
b	0.43	0.53	
D	1.00 BSC		
Е	0.60 BSC		
е	0.65 BSC		
L	0.20 0.30		

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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